



Ge surface cleaning

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Outlook



- Applied technique for Ge cleaning
 - Loading samples with the Rn daughters
 - Investigations of $^{210}\text{Pb}/^{210}\text{Bi}/^{210}\text{Po}$
- Ge surface treatment
 - Optical quality Ge
 - HPGe
 - Comparison with Copper and Steel
- Summary

Loading the samples

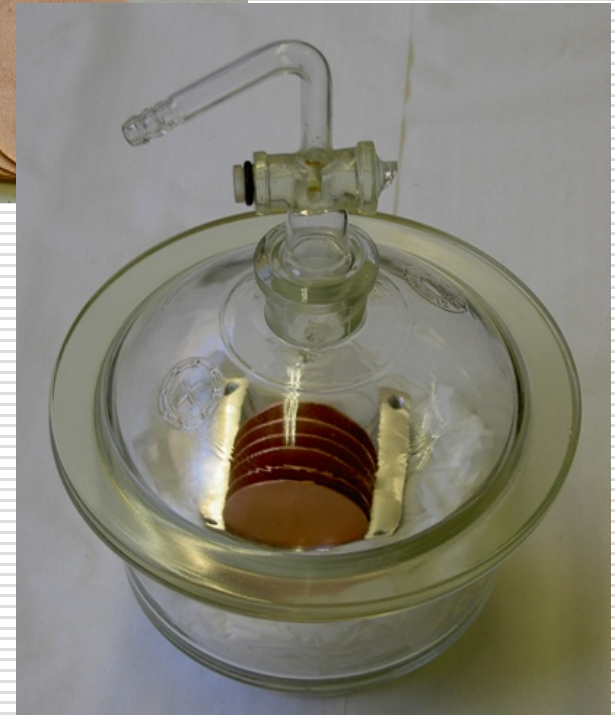
Filter

Discs



^{222}Rn
source
(1.4 MBq)

Pump





Measuring $^{210}\text{Pb}/^{210}\text{Bi}/^{210}\text{Po}$

- Screening of ^{210}Po with an alpha spectrometer
50 mm Si-detector, bcg $\sim 2 \alpha/d$ (1-10 MeV)
sensitivity $\sim 20 \text{ mBq/m}^2$ (100 mBq/kg, ^{210}Po)
- Screening of ^{210}Bi with a beta spectrometer
2×50 mm Si(Li)-detectors, bcg \sim
0.18/0.40 cpm sensitivity $\sim 10 \text{ Bq/kg}$ (^{210}Bi)
- Screening of ^{210}Pb (46.6 keV line) with a
gamma spectrometer 16 % - HPGe detector
with an active and a passive shield



Optical quality Germanium

- “Test run” before using HPGe
- Samples cut out from bigger Ge pieces, no special surface treatment after cutting
- 2 discs 50 mm in diameter and 3 mm thick were exposed for 7 months to our Rn source (1.4 MBq)
- Discs etched by Canberra according to their standard procedure applied to HPGe crystals
- Discs before/after etching were screened for $^{210}\text{Pb}/^{210}\text{Bi}/^{210}\text{Pb}$

Optical quality Germanium - results



Disc No. 1

Isotope	Disc side	Initial activity [cpm]	Activity after cleaning [cpm]	Reduction factor R	Average reduction factor R_{av}	Remarks
^{210}Pb	a	2.08	< 0.02	> 104	> 104	Amount of removed Ge not measured. After etching side b not measured for ^{210}Pb .
	b	3.43	-	-		
^{210}Bi	a	42.7	< 0.18	> 237	> 427	
	b	67.9	< 0.11	> 617		
^{210}Po	a	42.4	0.04	1060	2300	
	b	71.7	0.02	3585		



Optical quality Germanium - results

Disc No. 2

Isotope	Disc side	Initial activity [cpm]	Activity after cleaning [cpm]	Reduction factor R	Average reduction factor R_{av}	Remarks
^{210}Pb	a	2.09	-	-	> 106	Amount of removed Ge not measured. After etching side a not measured for ^{210}Pb . ^{210}Bi not measured because it has decayed.
	b	2.12	< 0.02	> 106		
^{210}Bi	a	40.7	-	-	-	
	b	46.1	-	-		
^{210}Po	a	50.0	0.06	820	880	
	b	47.0	0.05	940		

Activities of all isotopes reduced significantly after etching,
 ^{210}Po removed most efficiently

HPGe

- Two 50 mm in diameter and 3 mm thick HPGe discs provided by MPI-M
- One disc and HP water (2 L) exposed to the strong Rn source for 9 months
- Exposed disc etched by Canberra in their standard solution, clean disc etched in a solution made with the exposed water
- Discs before/after etching screened for $^{210}\text{Pb}/^{210}\text{Bi}/^{210}\text{Pb}$

HPGe discs loading



Drying column (Si-Geel)

Ge discs

Filter

HP Water

^{222}Rn
source
(1.4 MBq)

Pump



HPGe results

Exposed disc

	²¹⁰ Po	²¹⁰ Bi	²¹⁰ Pb
Before cleaning	11.88 ± 0.19	14.70 ± 0.12	0.717 ± 0.011
After cleaning	0.102 ± 0.006	0.017 ± 0.008	< 0.001
Reduction factor	117 ± 7	865 ± 407	> 717

Unexposed disc

	²¹⁰ Po	²¹⁰ Bi	²¹⁰ Pb
Before etching (background)	0.064 ± 0.005	0.111 ± 0.004	0.0163 ± 0.0004
After etching (average act. from both disc sides) bkg corrected!	0.023 ± 0.007	0.106 ± 0.011	0.0066 ± 0.0016
Increase above the background	~ 35 %	~ 100 %	~ 40 %

Exposed water measured with an HPGe spectrometer did not show any activity above the background (LLL in HD).



Comparison between Cu/Steel/Ge

Isotope	Average reduction factors for etching		
	Copper	Steel	Ge (Opt. – HP)
²¹⁰ Pb	~ 50	~ 100	100 – 700
²¹⁰ Bi	~ 50	~ 100	400 – 800
²¹⁰ Po	~ 1	~ 20	1000 – 100

- Etching of Copper is the less effective, for Po there is no effect
- Results for Steel are acceptable, also Po has been removed
- Etching of Ge is the most efficient, surface quality seems to play a role



Summary

- Etching of opt. Ge/HPGe removes efficiently all long-lived Rn daughters
- Small quantities of $^{210}\text{Pb}/^{210}\text{Bi}/^{210}\text{Po}$ found on the surface of the unexposed disc etched in the contaminated solution (the level of water contamination was unknown) - for each sample a fresh solution is required in order to avoid re-depositon
- ^{210}Po removed more efficient form optical quality Ge, $^{210}\text{Pb}/^{210}\text{Bi}$ from HPGe – surface quality plays a role
- Etching effectiveness in $^{210}\text{Pb}/^{210}\text{Bi}/^{210}\text{Po}$ removal differs for each isotope and for different materials (Cu, Steel, Ge)